

Amendments to the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-8 (Cancelled).

9. (Currently amended) A method of forming a transistor structure, comprising:
forming a transistor gate over a substrate, the transistor gate comprising a sidewall
which comprises electrically conductive material;
forming an electrically insulative material along the electrically conductive material of
the transistor gate sidewall; the electrically insulative material comprising at least two
separate layers; a first of the at least two layers comprising Al_pO_q , wherein p and q are
greater than 0 and less than 10; a second of the at least two layers consisting essentially of
silicon and nitrogen, the first of the at least two layers being disposed between the
transistor gate sidewall and the second of the at least two layers;
anisotropically etching the electrically insulative material to form a spacer along the
transistor gate sidewall; the anisotropically etching comprising etching both of the first and
second of the at least two layers; and
~~wherein the first of the at least two layers is between the second of the at least two~~
~~layers and the transistor gate sidewall~~
depositing a dopant barrier layer over the spacer; and
forming a doped oxide layer over the barrier layer.

10. (Original) The method of claim 9 further comprising implanting a dopant into the substrate and utilizing the spacer to align the dopant during the implant.

Claims 11-12(Cancelled).

13. (Previously amended) The method of claim 9 wherein the first of the at least two layers consists essentially of Al_pO_q .

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Claims 14-31 (Cancelled).

32. (Previously added) The method of claim 9 wherein the first of the at least two layers consists of Al_pO_q .

33. (Previously added) The method of claim 9 wherein the first of the at least two layers consists of Al_2O_3 .

34. (New) The method of claim 9 wherein the dopant barrier layer comprises silicon dioxide.

35. (New) The method of claim 9 wherein the doped oxide layer comprises BPSG.